

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2000-058777  
(43)Date of publication of application : 25.02.2000

(51)Int.Cl. H01L 27/108  
H01L 21/8242

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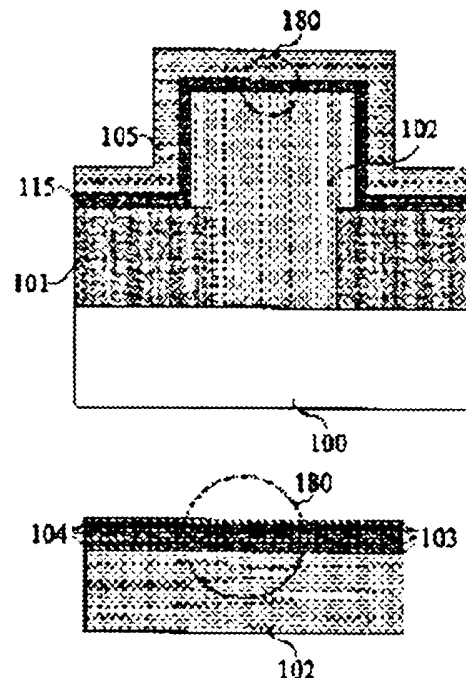
Priority number : 98 9832638 Priority date : 12.08.1998 Priority country : KR

(54) CAPACITOR COMPRISING ALUMINA/ALUMINUM NITRIDE COMPOSITE DIELECTRIC FILM FORMED BY ATOMIC LAYER VAPOR-DEPOSITION METHOD, AND ITS MANUFACTURE

(57)Abstract:

PROBLEM TO BE SOLVED: To trigger no chemical reaction even when a conductive polysilicon is used as a lower part electrode in succession in a semiconductor DRAM process, by forming a composite dielectric film comprising an alumina layer and an aluminum nitride layer on the upper part of a conductive layer with a pattern by an atomic layer vapor-deposition method.

SOLUTION: A silicon oxide film 101 is formed on a semiconductor substrate 100 first, and a storage polysilicon 102 is formed as a lower part electrode constituting a charge storage capacitor, over which an alumina 103 is formed by an atomic layer vapor-deposition method. Being amorphous, the alumina film is excellent in step coverage, almost to 100%. Then the alumina layer 103 and an aluminum nitride layer 104 are repeatedly formed by the atomic layer vapor-deposition method in situ, forming an  $\text{Al}_2\text{O}_3/\text{AlN}$  composite dielectric thin film 115, over which a doped polysilicon is vapor-deposited to form the upper part electrode of a DRAM capacitor.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of request for appeal]

[Date of appeal]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]